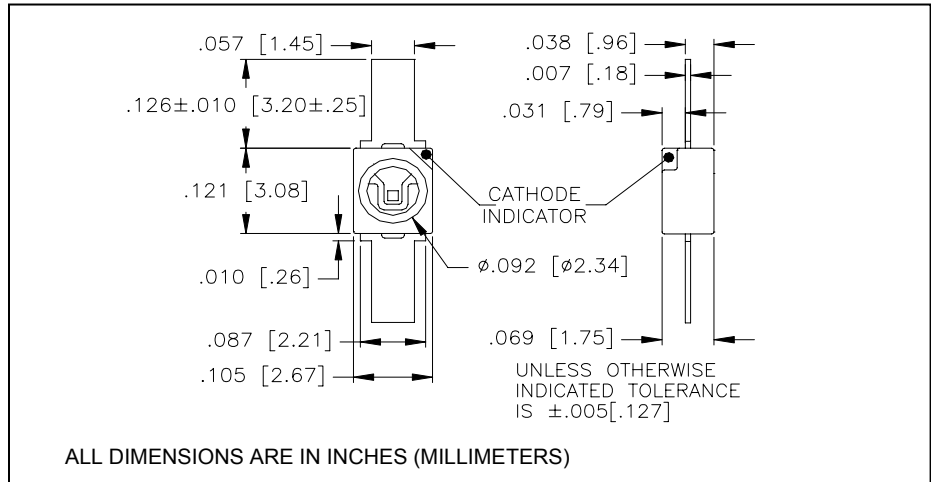


# CLE100F

## Gallium Arsenide IRED Flat Lead PLCC Package



August, 2001



### features

- Flat lead PLCC package
- $\pm 50^\circ$  emission angle
- 940 nm peak wavelength

### description

The CLE100F is a 940nm infrared emitting diode featuring current GaAs/AlGaAs technology for increased quantum efficiency. The chip is mounted in a compact, embedded leadframe package with flying lead configuration and overcoated with clear epoxy to provide a wide emission pattern. Different wavelength chips, different lenses and different lead configurations are available. For additional information, call Clairex.

### absolute maximum ratings ( $T_A = 25^\circ\text{C}$ unless otherwise stated)

storage temperature	-40°C to +125°C
operating temperature	-40°C to +100°C
lead soldering temperature <sup>(1)</sup>	260°C
continuous forward current <sup>(2)</sup>	30mA
peak forward current (1.0ms pulse width, 10% duty cycle)	1A
reverse voltage	5V
continuous power dissipation <sup>(3)</sup>	75mW

### notes:

1. 0.06" (1.5mm) from case for 5 seconds maximum.
2. Derate linearly 0.32mA/°C from 25°C free air temperature to  $T_A = +100^\circ\text{C}$ .
3. Derate linearly 0.80mW/°C from 25°C free air temperature to  $T_A = +100^\circ\text{C}$ .

### electrical characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

symbol	parameter	min	typ	max	units	test conditions
$P_O$	Total power output	2.0	2.5	-	mW	$I_F = 20\text{mA}$
$V_F$	Forward voltage	-	-	1.5	V	$I_F = 20\text{mA}$
$I_R$	Reverse current	-	-	10	$\mu\text{A}$	$V_R = 5.0\text{V}$
$\lambda_p$	Peak emission wavelength	-	940	-	nm	$I_F = 20\text{mA}$
BW	Spectral bandwidth at half power points	-	50	-	nm	$I_F = 20\text{mA}$
$\theta_{HP}$	Emission angle at half power points	-	100	-	deg.	$I_F = 20\text{mA}$
$t_r, t_f$	Radiation rise and fall time	-	700	-	ns	$I_{F(PK)} = 20\text{mA}$

Clairex reserves the right to make changes at any time to improve design and to provide the best possible

Revised 3/15/06